

Silicon Epitaxial Planar Schottky Barrier Diode

Features

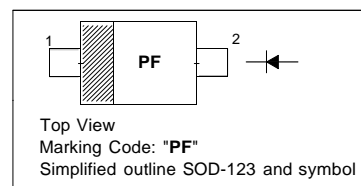
- High reliability
- Low forward voltage

Application

- For switching power supplies
- Battery protection against reversal current

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	40	V
Reverse Voltage	V_R	40	V
Average Rectified Forward Current	$I_{F(AV)}$	1	A
Peak Forward Surge Current (8.3 ms)	I_{FSM}	30	A
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\text{ A}$	V_F	0.51	V
Reverse Current at $V_R = 40\text{ V}$	I_R	30	μA



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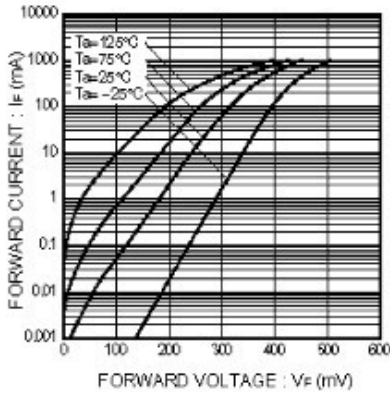


Fig.1 Forward Temperature Characteristics

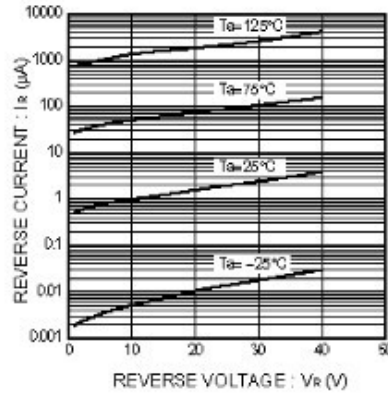


Fig.2 Reverse Temperature Characteristics

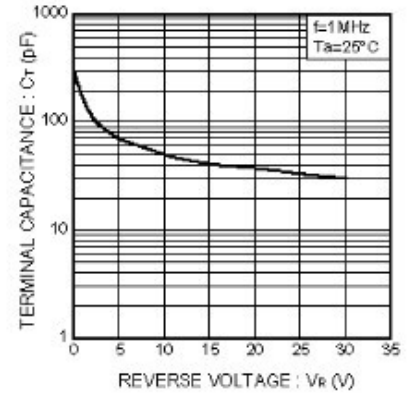


Fig.3 Capacitance Between Terminals Characteristics

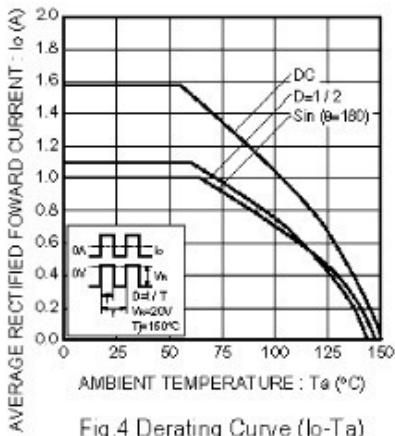


Fig.4 Derating Curve (I_o - T_a)

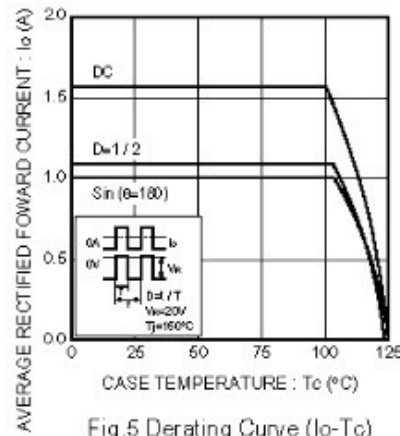


Fig.5 Derating Curve (I_o - T_c)

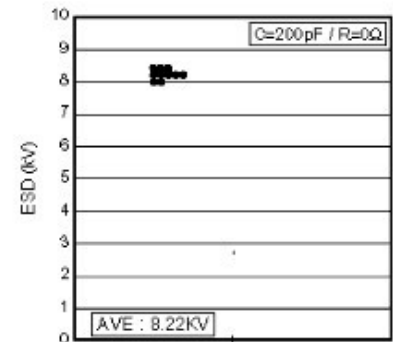


Fig.6 ESD